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22. “RHEED Studies of Heterojunction and Quantum Well Formation during
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27. “Growth of Quantum Well Heterostructures by MBE for Short Wavelength
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29. “Growth of GaAs on Si”, K. Woodbridge (invited), presented at the
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30. “Geometrical Dependence of Transient Nonlinearities in Multiple Quantum
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84. Other Meeting Presentations – Not Refereed


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Book Chapter

Refereed Journal Publications


20. “Dependence of Threshold Current on the Number of Wells in AlGaAs-
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21. “Short Wavelength (Visible) Quantum Well Lasers grown by Molecular
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22. “RHEED Studies of Heterojunction and Quantum Well Formation during
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23. “Magneto- Optics in GaAs-GaAlAs Quantum Wells”, D.C. Rogers, J.
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JOURNAL PUBLICATIONS ACCEPTED OR IN REVIEW


